High-Current Complementary Silicon Transistors

... for use as output devices in complementary general purpose amplifier applications.

- High DC Current Gain hFE = 1000 (Min) @ I $_{\rm C}$ = 25 Adc hFE = 400 (Min) @ I $_{\rm C}$ = 50 Adc
- Curves to 100 A (Pulsed)
- Diode Protection to Rated IC
- Monolithic Construction with Built-In Base-Emitter Shunt Resistor
- Junction Temperature to +200°C

MAXIMUM RATINGS

Rating	Symbol	MJ11028 MJ11029	MJ11030 MJ11031	MJ11032 MJ11033	Unit
Collector–Emitter Voltage	VCEO	60	90	120	Vdc
Collector-Base Voltage	V _{CB}	60	90	120	Vdc
Emitter-Base Voltage	V _{EB}	5			Vdc
Collector Current — Continuous Peak	I _C	50 100			Adc
Base Current — Continuous	ΙΒ	2			Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C @ T _C = 100°C	PD	300 1.71			Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-	-55 to +200)	°C

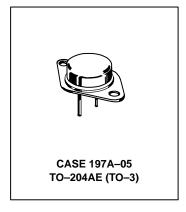
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Maximum Lead Temperature for Soldering Purposes for ≤ 10 seconds	TL	275	°C
Thermal Resistance Junction to Case	$R_{ heta JC}$	0.584	°C

MJ11028 MJ11030 MJ11032* MJ11029 MJ11031 MJ11033*

*Motorola Preferred Device

50 AMPERE
COMPLEMENTARY
SILICON
DARLINGTON
POWER TRANSISTORS
60-120 VOLTS
300 WATTS



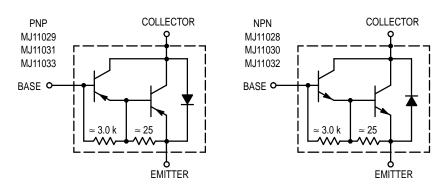


Figure 1. Darlington Circuit Schematic

Preferred devices are Motorola recommended choices for future use and best overall value.



MJ11028 MJ11030 MJ11032 MJ11029 MJ11031 MJ11033

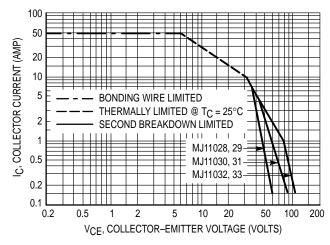
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					•
Collector–Emitter Breakdown Voltage (1) (I _C = 1 00 mAdc, I _B = 0)	MJ11028, MJ11029 MJ11030, MJ11031 MJ11032, MJ11033	V(BR)CEO	60 90 120	_ _ _	Vdc
Collector-Emitter Leakage Current (VCE = 60 Vdc, RBE = 1 k ohm) (VCE = 90 Vdc, RBE = 1 k ohm) (VCE = 120 Vdc, RBE = 1 k ohm) (VCE = 60 Vdc, RBE = 1 k ohm, TC = 150°C) (VCE = 90 Vdc, RBE = 1 k ohm, TC = 150°C) (VCE = 120 Vdc, RBE = 1 k ohm, TC = 150°C) Emitter Cutoff Current (VBE = 5 Vdc, IC = 0)	MJ11028, MJ11029 MJ11030, MJ11031 MJ11032, MJ11033 MJ11028, MJ11029 MJ11030, MJ11031 MJ11032, MJ11033	ICER	 	2 2 2 10 10 10	mAdc
Collector–Emitter Leakage Current (V _{CE} = 50 Vdc, I _B = 0)		ICEO	_	2	mAdc
ON CHARACTERISTICS (1)			1		
DC Current Gain (I _C = 25 Adc, V _{CE} = 5 Vdc) (I _C = 50 Adc, V _{CE} = 5 Vdc)		h _{FE}	1 k 400	18 k —	_
Collector–Emitter Saturation Voltage (I _C = 25 Adc, I _B = 250 mAdc) (I _C = 50 Adc, I _B = 500 mAdc)		VCE(sat)	_ _	2.5 3.5	Vdc
Base–Emitter Saturation Voltage		V _{BE} (sat)			Vdc

(1) Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

 $(I_C = 25 \text{ Adc}, I_B = 200 \text{ mAdc})$

 $(I_C = 50 \text{ Adc}, I_B = 300 \text{ mAdc})$



There are two limitations on the power-handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC - VCE limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

3.0

4.5

The data of Figure 2 is based on $T_{J(pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

Figure 2. DC Safe Operating Area

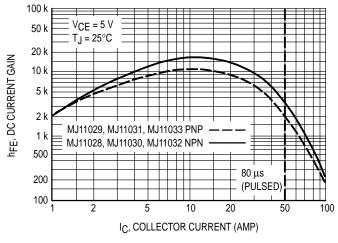


Figure 3. DC Current Gain

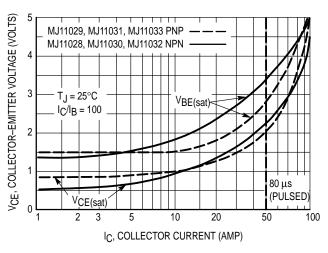
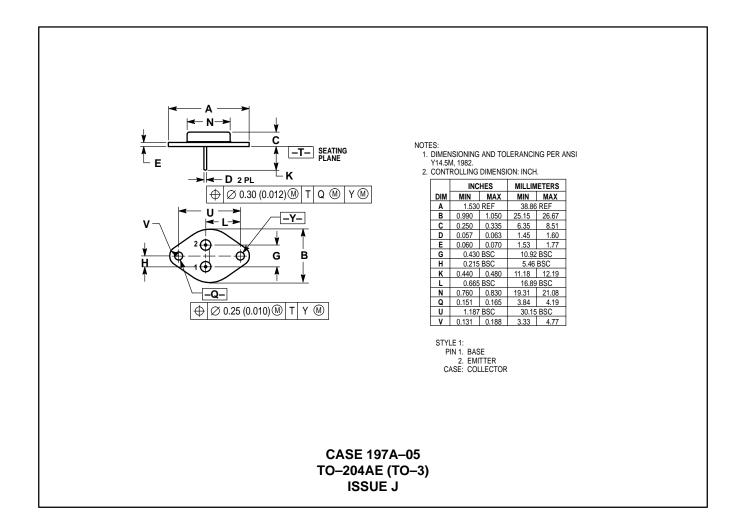


Figure 4. "On" Voltage

MJ11028 MJ11030 MJ11032 MJ11029 MJ11031 MJ11033

PACKAGE DIMENSIONS



MJ11028 MJ11030 MJ11032 MJ11029 MJ11031 MJ11033

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